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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet 1 of 1

Application Number 09/941,453

Filing Date 08/28/2001

First Named Inventor: Fang-Cheng Chang

Examiner name: J. Mancuso

GROUP: 2623 1756

Mohamedulla

Attorney Docket Number NTI-024

Technology Center 2600

**U.S. PUBLISHED APPLICATION DOCUMENTS**

Examiner Initials*	Cited No. <sup>1</sup>	U.S. Patent Document Number	Kind Code <sup>2</sup> (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines Where Relevant Info. Appear
SRM	A01	2001/0004122	A1	Ito	06/21/2001	
SRM	A02	2001/0005619	A1	Hasebe et al.	06/28/2001	

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cited No. <sup>1</sup>	U.S. Patent Document Number	Kind Code <sup>2</sup> (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines Where Relevant Info. Appear
SRM	B01	5597668		Nowak et al.	01/28/1997	

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cited No. <sup>1</sup>	Foreign Patent Document Office <sup>3</sup> Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines Where Relevant Info. Appear	T <sup>6</sup>

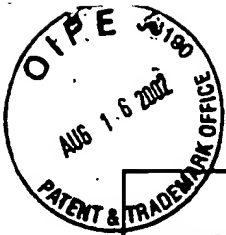
**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**


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<sup>1</sup>Unique citation designation number. <sup>2</sup>See attached Kinds of U.S. Patent Documents. <sup>3</sup>Enter Office that issued the document by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.

SHEET 1 of 2**INFORMATION DISCLOSURE  
CITATION****PTO-1449****Atty. Docket No.**

NTI-024

**Serial No.**

09/941,453-6364

**Applicant**

CHANG, Fang-Cheng

**Filing Date**

8/28/2001

**Group**1756  
~~Not Yet Assigned~~**U.S. PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
SRM	6,016,357	1/18/2000	Neary, et al.	382	144	6/16/1997
SRM	6,023,328	2/8/2000	Pierrat	356	237.4	2/23/1998
SRM	6,076,465	6/20/2000	Vacca, et al.	101	481	9/19/1997
SRM	6,091,845	7/18/2000	Pierrat, et al.	382	144	2/24/1998
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SHEET 2 of 3INFORMATION DISCLOSURE  
CITATION

PTO-1449

Atty. Docket No.

NTI-024

Serial No.

09/941,453-6364

Applicant

CHANG, Fang-Cheng

Filing Date

8/28/2001

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## FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
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<i>SM</i>	WO 97/13370	4/10/1997	WO	—	—	<input type="checkbox"/>	<input type="checkbox"/>
<i>SM</i>	WO 98/20327	5/14/1998	WO	—	—	<input type="checkbox"/>	<input type="checkbox"/>
<i>SM</i>	WO 98/45685	10/15/1998	WO	—	—	<input type="checkbox"/>	<input type="checkbox"/>
<i>SM</i>	WO 99/38002	7/29/1999	WO	—	—	<input type="checkbox"/>	<input type="checkbox"/>
<i>SM</i>	WO 99/56113	11/4/1999	WO	—	—	<input type="checkbox"/>	<input type="checkbox"/>
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<i>SM</i>	WO 99/67626	12/29/1999	WO	—	—	<input type="checkbox"/>	<input type="checkbox"/>
<i>SM</i>	WO 99/14706 A2/A3	3/25/1999	WO	—	—	<input type="checkbox"/>	<input type="checkbox"/>

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<del>SM</del>	<del>Fiekowsky, P., et al., "Defect Printability Measurement on the KLA-351: Correlation to Defect Sizing Using the AVI Metrology System", SPIE 19th Annual BACUS Symposium on Photomask Technology and Management Conference, pp. 1-6, September 1999.</del>
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<b>INFORMATION DISCLOSURE</b> <b>CITATION</b> 	<b>Atty. Docket No.</b> NTI-024	<b>Serial No.</b> 09/941,453-6364
	<b>Applicant</b> CHANG, Fang-Cheng	
	<b>Filing Date</b> 8/28/2001	<b>Group</b> 1756 Not Yet Assigned

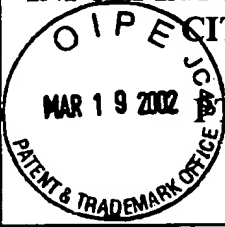
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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
SRM	5,326,659	7/5/1994	Liu, et al.	430	5	3/5/1992
↑	5,340,700	8/23/1994	Chen, et al.	430	312	11/3/1993
↑	5,432,714	7/11/1995	Chung, et al.	364	525	9/2/1994
↑	5,572,598	11/5/1996	Wihl, et al.	382	144	2/25/1994
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↑	5,801,954	9/1/1998	Le, et al.	364	488	4/24/1996
↑	5,804,340	9/8/1998	Garza, et al.	430	5	12/23/1996
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↑	5,825,647	10/20/1998	Tsudaka	364	167.03	3/12/1996
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↑	6,009,250	12/28/1999	Ho, et al.	395	500.06	9/30/1997
↑	6,009,251	12/28/1999	Ho, et al.	395	500.06	9/30/1997
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↑	6,078,738	6/20/2000	Garza, et al.	395	500.22	5/8/1997
↓	6,081,659	6/27/2000	Garza, et al.	395	500.22	4/26/1999
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<b>INFORMATION DISCLOSURE</b> <b>CITATION</b>  <b>PTO-1449</b>		<b>Atty. Docket No.</b> NTI-024		<b>Serial No.</b> 09/941,453-6344			
		<b>Applicant</b> CHANG, Fang-Cheng		<b>Group</b> 1756 <del>Not Yet Assigned</del>			
		<b>Filing Date</b> 8/28/2001		Technology Center 2600 MAR 21 2002 <b>RECEIVED</b>			
<b>FOREIGN PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
SRM	WO 00/36525 A2	6/22/2000	WO	/	/	<input type="checkbox"/>	<input type="checkbox"/>
SRM	WO 00/67074 A1	11/9/2000	WO	/	/	<input type="checkbox"/>	<input type="checkbox"/>
SRM	WO 00/67075 A1	11/9/2000	WO	/	/	<input type="checkbox"/>	<input type="checkbox"/>
SRM	WO 00/67076 A1	11/9/2000	WO	/	/	<input type="checkbox"/>	<input type="checkbox"/>


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<b>INFORMATION DISCLOSURE CITATION</b> 		<b>Atty. Docket No.</b> NTI-024 <b>Applicant</b> CHANG, Fang-Cheng <b>Filing Date</b> 8/28/2001	<b>Serial No.</b> 09/941,453-6364 <b>Group</b> 1786 <del>Not Yet Assigned</del>
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>			
<b>EXAMINER'S INITIALS</b>	<b>CITATION</b>		
	Cobb, et al., "Fast Sparse Aerial Image Calculation for OPC", SPIE, Vol. 2621, pp. 534-544.		
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<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>			
<b>EXAMINER'S INITIALS</b>	<b>CITATION</b>		
AM	Ham, Y.M., et al., "Dependence of Defects in Optical Lithography", Jpn. J. Appl. Phys., Vol. 31, pp. 4137-4142 (1992).		
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<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>			
<b>EXAMINER'S INITIALS</b>	<b>CITATION</b>		
<i>SRM</i>	Chang, K., et al., "Accurate Modeling of Deep Submicron Interconnect Technology", TMA Times, Vol. IX, No. 3 (1997).		
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	<b>Applicant</b> CHANG, Fang-Cheng	
	<b>Filing Date</b> 8/28/2001	<b>Group</b> 172 <del>2623</del>

**U.S. PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
SKM	6,130,750	10/10/2000	Ausschnitt, et al.	356	401	8/28/1997
SKM	6,346,426 B1	2/12/2002	Toprac, et al.	438	8	11/17/2000

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Applicant

CHANG, Fang-Cheng

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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
SPM	2002/0164064 A1	11/7/2002	Karklin, et al.	382	145	3/20/2001
SPM	2002/0164065 A1	11/7/2002	Cai, et al.	382	149	3/20/2001

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SHEET 3 of 3

<b>INFORMATION DISCLOSURE CITATION</b>  <b>PTO-1449</b>		<b>Atty. Docket No.</b> NTI-024	<b>Serial No.</b> 09/941,453
		<b>Applicant</b> CHANG, Fang-Cheng	<b>Group</b> 2623-1756
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>			
<b>EXAMINER'S INITIALS</b>	<b>CITATION</b>		
<i>SM</i>	Lin, B.J., et al., "Single-Level Electric Testsites for Phase-Shifting Masks", SPIE, Vol. 1673, pp. 221-228, March 9-11, 1992.		

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